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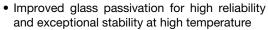
Vishay Semiconductors

Medium Power Phase Control Thyristors (Stud Version), 22 A



PRIMARY CHARACTERISTICS					
I _{T(AV)}	22 A				
V _{DRM} /V _{RRM}	100 V, 200 V, 400 V, 600 V, 800 V, 1000 V, 1200 V				
V_{TM}	1.70 V				
I _{GT}	60 mA				
T _J	-65 °C to +125 °C				
Package	TO-48 (TO-208AA)				
Circuit configuration	Single SCR				

FEATURES





- High dl/dt and dV/dt capabilities
- Standard package
- · Low thermal resistance
- · Metric threads version available
- Types up to 1200 V V_{DRM}/V_{RRM}
- Designed and qualified for industrial and consumer level
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

TYPICAL APPLICATIONS

- Medium power switching
- · Phase control applications

MAJOR RATINGS AND CHARACTERISTICS						
PARAMETER	TEST CONDITIONS	VALUES	UNITS			
1		22	Α			
$I_{T(AV)}$	T _C	85	°C			
I _{T(RMS)}		35	А			
I _{TSM}	50 Hz	400	^			
	60 Hz	420	A			
I ² t	50 Hz	793	A ² s			
1-1	60 Hz	724	A-S			
V _{DRM} /V _{RRM}		100 to 1200	V			
tq	Typical	110	μs			
T _J		-65 to +125	°C			

ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS								
TYPE NUMBER	VOLTAGE CODE	V _{DRM} /V _{RRM} , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE ⁽¹⁾ V	V _{RSM} , MAXIMUM NON-REPETITIVE PEAK VOLTAGE ⁽²⁾ V	$\begin{aligned} I_{DRM}/I_{RRM} & \text{MAXIMUM} \\ \text{ATT}_J = T_J & \text{MAXIMUM} \\ & \text{mA} \end{aligned}$				
	10	100	150	20				
	20	200	300					
	40	400	400 500					
VS-22RIA	60	600	700	10				
	80	800	900	10				
	100	1000	1100					
	120	1200	1300					

Notes

(1) Units may be broken over non-repetitively in the off-state direction without damage, if dl/dt does not exceed 20 A/µs

⁽²⁾ For voltage pulses with $t_p \le 5$ ms



PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS	
Maximum average on-state current		1000 einus	180° sinusoidal conduction		22	Α
at case temperature	I _{T(AV)}	160 Sinusc	dai conduction		85	°C
Maximum RMS on-state current	I _{T(RMS)}				35	Α
		t = 10 ms	No voltage		400	
Maximum peak, one-cycle		t = 8.3 ms	reapplied		420	1
non-repetitive surge current	I _{TSM}	t = 10 ms	100 % V _{RRM}		335	A
		t = 8.3 ms	reapplied	Sinusoidal half wave,	355	
Maximum I ² t for fusing		t = 10 ms	No voltage initial T _J =T _J maxin reapplied	initial T _J =T _J maximum	793	- A ² s
	l ² t	t = 8.3 ms			724	
		t = 10 ms	100 % V _{RRM}		560	
		t = 8.3 ms	reapplied		515	
Maximum $I^2 \sqrt{t}$ for fusing	I²√t	$t=0.1$ to 10 ms, no voltage reapplied, $T_J=T_J$ maximum		7930	A²√s	
Low level value of threshold voltage	V _{T(TO)1}	(16.7 % x π x $I_{T(AV)}$ < I < π x $I_{T(AV)}$), $T_J = T_J$ maximum		0.83	V	
High level value of threshold voltage	V _{T(TO)2}	$(I > \pi \times I_{T(AV)})$	$(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$		0.95	V
Low level value of on-state slope resistance	r _{t1}	(16.7 % x π x I _{T(AV)} < I < π x I _{T(AV)}), T _J = T _J maximum		14.9	~ 0	
High level value of on-state slope resistance	r _{t2}	$(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$		13.4	- mΩ	
Maximum on-state voltage	V _{TM}	I _{pk} = 70 A, T _J = 25 °C		1.70	V	
Maximum holding current	I _H	T _ 05 °C	anada aunnis 6	V registive lead	130	
Latching current	ΙL	T _J = 25 °C, anode supply 6 V, resistive load		200	mA	

SWITCHING						
PARAMETER		SYMBOL TEST CONDITIONS		VALUES	UNITS	
	$V_{DRM} \le 600 \text{ V}$			200		
Maximum rate of rise	$V_{DRM} \le 800 \text{ V}$	dl/dt	$T_J = T_J$ maximum, $V_{DM} = Rated\ V_{DRM}$ Gate pulse = 20 V, 15 Ω , $t_p = 6$ μs , $t_r = 0.1$ μs maximum $I_{TM} = (2\ x\ rated\ dl/dt)\ A$	180	A/μs	
of turned-on current	$V_{DRM} \le 1000 \text{ V}$	ai/at		160		
	$V_{DRM} \le 1600 \text{ V}$			150		
Typical turn-on time		t _{gt}	$T_J = 25$ °C, at rated V_{DRM}/V_{RRM} , $T_J = 125$ °C	0.9		
Typical reverse recovery time		t _{rr}	$T_J = T_J$ maximum, $I_{TM} = I_{T(AV)}$, $t_p > 200 \ \mu s$, $dI/dt = -10 \ A/\mu s$	4	μs	
Typical turn-off time		t _q	$T_J=T_J$ maximum, $I_{TM}=I_{T(AV)},t_p>200~\mu s,V_R=100~V,dI/dt=$ - 10 A/µs, dV/dt = 20 V/µs linear to 67 % $V_{DRM},$ gate bias 0 V to 100 W	110	, -	

Note

• $t_q = 10 \mu s$ up to 600 V, $t_q = 30 \mu s$ up to 1600 V available on special request

BLOCKING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum critical rate of rise	dV/dt	T _J = T _J maximum linear to 100 % rated V _{DRM}	100	V/µs
of off-state voltage	uv/ut	T _J = T _J maximum linear to 67 % rated V _{DRM}	300 (1)	V/μS

Note

(1) Available with: $dV/dt = 1000 V/\mu s$, to complete code add S90 i.e. 22RIA120S90



TRIGGERING					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum peak gate power	P _{GM}	$T_{il} = T_{il}$ maximum		8.0	W
Maximum average gate power	P _{G(AV)}	T J = T J Maximum		2.0	VV
Maximum peak positive gate current	I _{GM}	$T_J = T_J$ maximum		1.5	Α
Maximum peak negative gate voltage	-V _{GM}	$T_J = T_J$ maximum		10	V
		T _J = - 65 °C		90	
DC gate current required to trigger	I _{GT}	T _J = 25 °C	Maximum required gate trigger current/voltage are the lowest value which will trigger all units 6 V anode to cathode applied	60	mA
		T _J = 125 °C		35	
	V _{GT}	T _J = - 65 °C		3.0	V
DC gate voltage required to trigger		T _J = 25 °C		2.0	
		T _J = 125 °C		1.0	
DC gate current not to trigger	I _{GD}	T _J = T _J maximum, V _{DRM} = Rated value		2.0	mA
DC gate voltage not to trigger	V_{GD}	$T_J = T_J \text{ maximum},$ $V_{DRM} = \text{Rated value}$	Maximum gate current/voltage not to trigger is the maximum value which will not trigger any unit with rated V _{DRM} anode to cathode applied	0.2	٧

THERMAL AND MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	VAL	VALUES		
Maximum operating junction and storage temperature range	T _J , T _{Stg}		-65 to +125		°C	
Maximum thermal resistance, junction to case	R _{thJC}	DC operation 0.86		14004		
Maximum thermal resistance, case to heat sink	R _{thCS}	Mounting surface, smooth, flat and greased 0.35		35	K/W	
			TO NUT	TO DEVICE		
			20 (27.5)	25	lbf ⋅ in	
Mounting torque		Lubricated threads (Non-lubricated threads)	0.23 (0.32)	0.29	kgf · m	
	(Non labilitation times		2.3 (3.1)	2.8	N · m	
Approximate weight			1	4	g	
Approximate weight			0.	49	OZ.	
Case style		See dimensions - link at the end of datasheet	TO-48 (TO-208AA)		A)	

△R _{thJC} CONDUCTION				
CONDUCTION ANGLE	SINUSOIDAL CONDUCTION	RECTANGULAR CONDUCTION	TEST CONDITIONS	UNITS
180°	0.21	0.15		
120°	0.25	0.25		
90°	0.31	0.34	$T_J = T_J$ maximum	K/W
60°	0.45	0.47		
30°	0.76	0.76		

Note

• The table above shows the increment of thermal resistance RthJC when devices operate at different conduction angles than DC

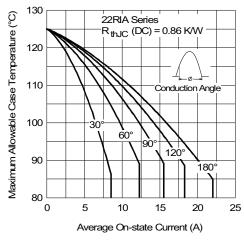


Fig. 1 - Current Ratings Characteristics

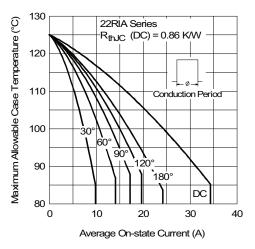


Fig. 1 - Current Ratings Characteristics

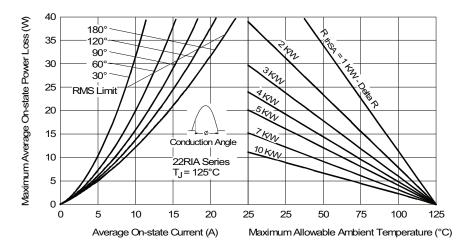


Fig. 2 - On-State Power Loss Characteristics

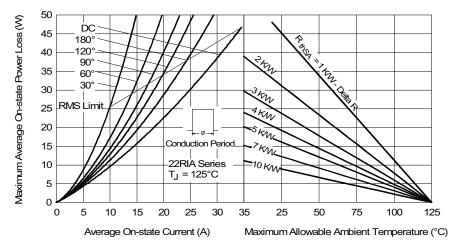


Fig. 3 - On-State Power Loss Characteristics

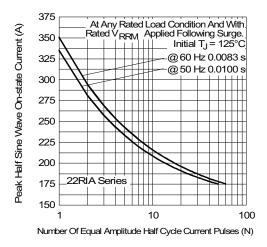


Fig. 4 - Maximum Non-Repetitive Surge Current

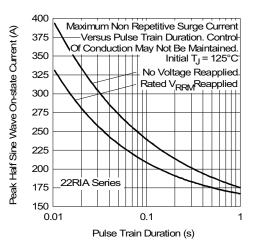


Fig. 5 - Maximum Non-Repetitive Surge Current

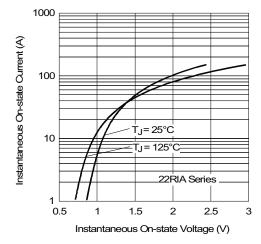


Fig. 6 - Forward Voltage Drop Characteristics

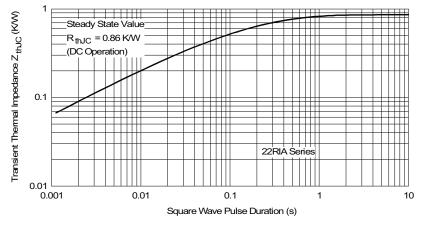


Fig. 7 - Thermal Impedance Z_{thJC} Characteristics

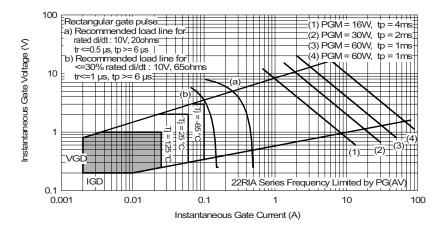
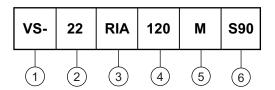


Fig. 8 - Gate Characteristics

ORDERING INFORMATION TABLE

Device code



- 1 Vishay Semiconductors product
- 2 Current code
- 3 Essential part number
- Voltage code x 10 = V_{RRM} (see Voltage Ratings table)
- 5 None = stud base TO-48 (TO-208AA) 1/4" 28UNF-2A
- M = stud base TO-48 (TO-208AA) M6 x 1
- 6 Critical dV/dt:

None = 300 V/µs (standard value)

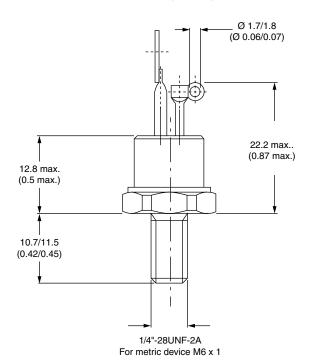
S90 = 1000 V/µs (special selection)

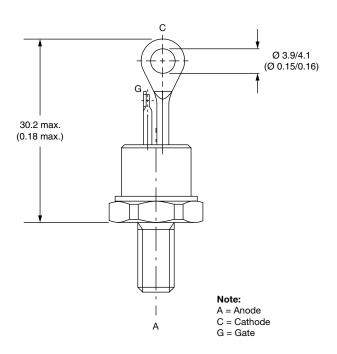
LINKS TO RELAT	ED DOCUMENTS
Dimensions	www.vishay.com/doc?95333

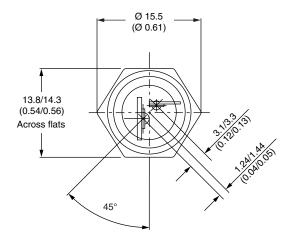


TO-208AA (TO-48)

DIMENSIONS in millimeters (inches)







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